

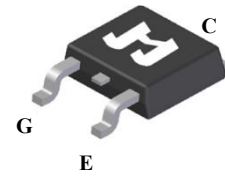
Key performance:

- $V_{CE}=650V$
- $I_C=6A@T_C=100^{\circ}C$
- $V_{CE(sat)}=1.7 V$

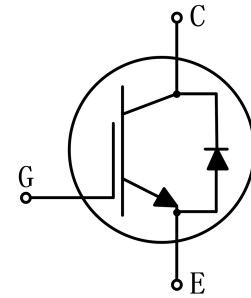
TO-252

Features:

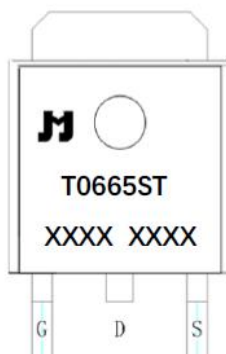
- High ruggedness performance
- Very tight parameter distribution
- Positive $V_{CE(sat)}$ temperature coefficient
- High efficiency for motor control
- Excellent current sharing in parallel operation
- RoHS compliant


Applications:

- Home appliances
- Motor drives
- Fan, Pumps, Vacuum cleaner


Package parameters

Type	Marking	Package	Packaging method
JJT6N65ST	T0665ST	TO-252	Tape and reel



XXXX XXXX
 Wafer Lot Number Datecode-YYWW

Maximum ratings

Symbol	Parameter	Values	Unit
V_{CES}	Collector-emitter voltage	650	V
V_{GES}	Gate-emitter voltage	±20	V
I_C	Continuous collector current ($T_C=25^\circ\text{C}$)	12	A
	Continuous collector current ($T_C=100^\circ\text{C}$)	6	A
I_{CM}	Pulsed collector current, t_p limited by T_{vjmax}	24	A
I_F	Diode continuous forward current ($T_C=100^\circ\text{C}$)	6	A
I_{FM}	Diode maximum current, t_p limited by T_{vjmax}	24	A
t_{sc}	Short circuit withstand time	10	μs
P_{tot}	Power dissipation ($T_C=25^\circ\text{C}$)	60	W
	Power dissipation ($T_C=100^\circ\text{C}$)	30	W
T_{vj}	Operating junction temperature range	-40 to +175	°C
T_{STG}	Storage temperature range	-55 to +150	°C

Thermal characteristics

Symbol	Parameter	Values		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Thermal resistance, junction to case for IGBT	-	2.5	K/ W
$R_{th(j-c)}$	Thermal resistance, junction to case for Diode	-	4.6	K/ W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	-	50	K/ W

Switching characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=400V$ $V_{GE}=0/15V$ $I_C=6A$ $R_G=10\Omega$ Inductive load	-	10	-	ns
t_r	Rise time		-	8	-	ns
$t_{d(off)}$	Turn-off delay time		-	79	-	ns
t_f	Fall time		-	56	-	ns
E_{on}	Turn-on energy		-	0.11	-	mJ
E_{off}	Turn-off energy		-	0.10	-	mJ
E_{ts}	Total switching energy		-	0.21	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CC}=400V$ $V_{GE}=0/15V$ $I_C=6A$ $R_G=10\Omega$ Inductive Load $T_{vj}=175^\circ C$	-	11	-	ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	108	-	ns
t_f	Fall time		-	89	-	ns
E_{on}	Turn-on energy		-	0.16	-	mJ
E_{off}	Turn-off energy		-	0.16	-	mJ
E_{ts}	Total switching energy		-	0.32	-	mJ

Electrical characteristics of Diode ($T_{vj}=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
V_F	Diode forward voltage	$I_F=6\text{A}$	-	1.6	-	V
		$I_F=6\text{A}, T_{vj}=175^{\circ}\text{C}$	-	1.4	-	V
t_{rr}	Diode reverse recovery time	$V_R=400\text{V}$ $I_F=6\text{A}$ $di_F/dt=-500\text{A}/\mu\text{s}$	-	55	-	ns
I_{rrm}	Diode peak reverse recovery current		-	10	-	A
Q_{rr}	Diode reverse recovery charge		-	306	-	nC
t_{rr}	Diode reverse recovery time	$V_R=400\text{V}$ $I_F=6\text{A}$ $di_F/dt=-500\text{A}/\mu\text{s}$ $T_{vj}=175^{\circ}\text{C}$	-	98	-	ns
I_{rrm}	Diode peak reverse recovery current		-	12	-	A
Q_{rr}	Diode reverse recovery charge		-	529	-	nC

Typical performance characteristics

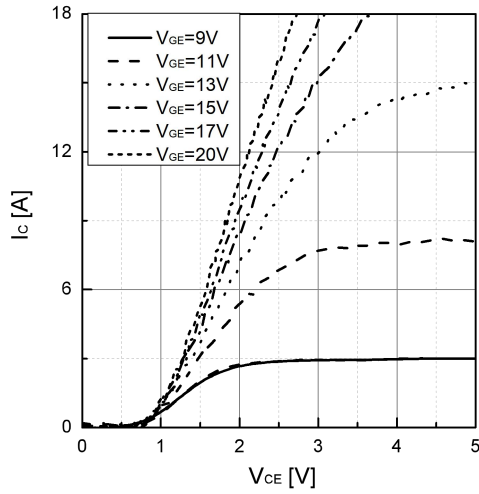


Fig 1. Typical output characteristic ($T_{vj}=25^{\circ}\text{C}$)

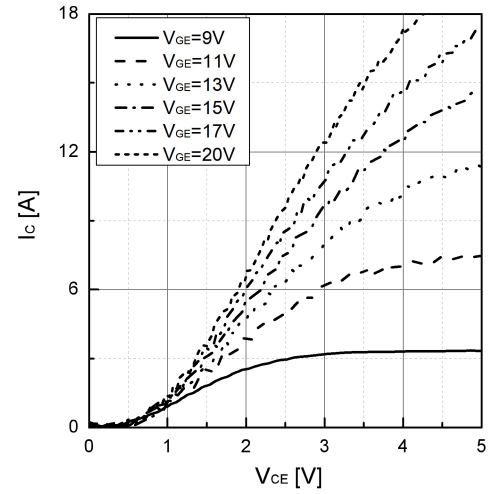


Fig 2. Typical output characteristic ($T_{vj}=175^{\circ}\text{C}$)

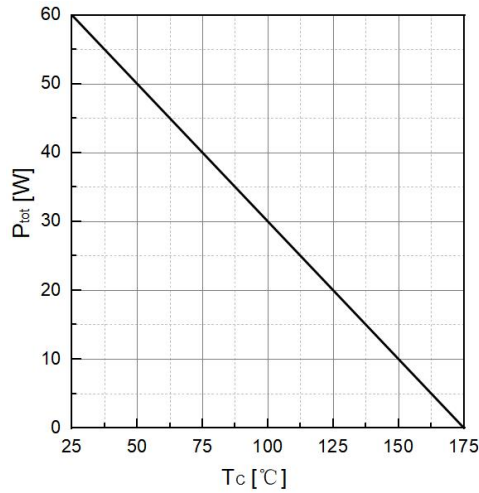


Fig 3. Power dissipation as a function of T_c

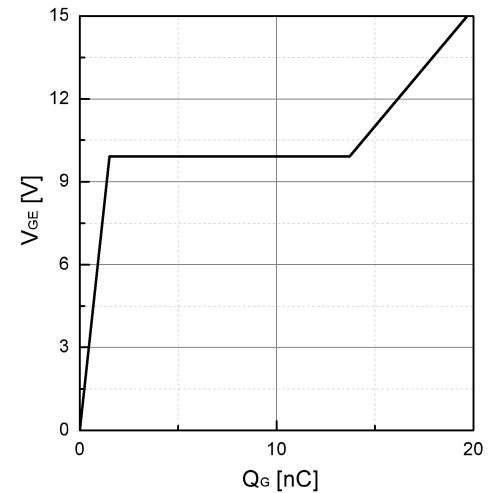


Fig 4. Typical Gate charge

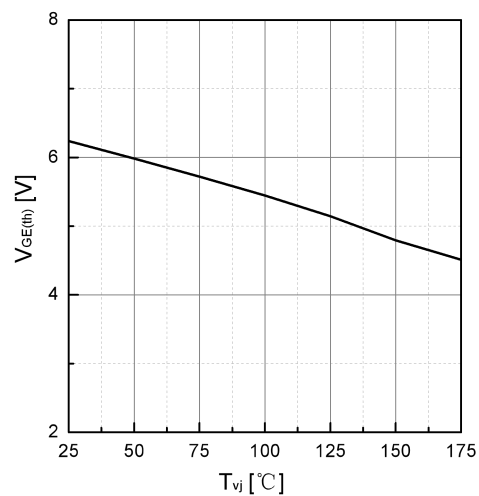


Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj}
($I_c=1\text{mA}$)

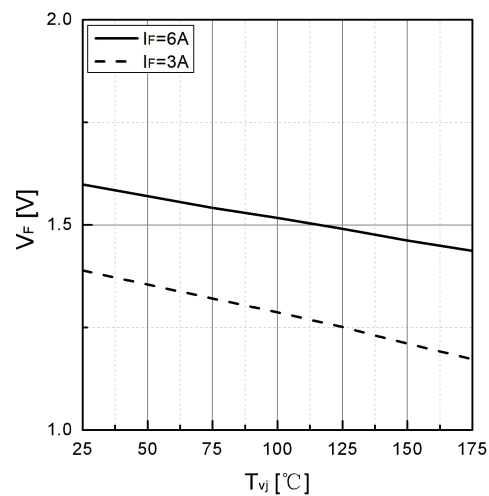


Fig 6. Typical V_F as a function of T_{vj}

Typical performance characteristics

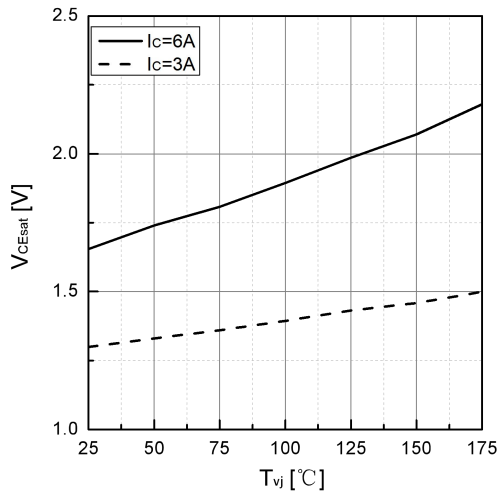


Fig 7. Typical V_{CEsat} as a function of T_{vj}

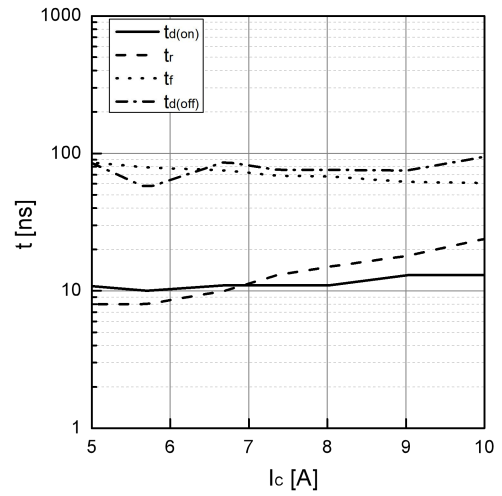


Fig 8. Typical switching time as a function of I_c

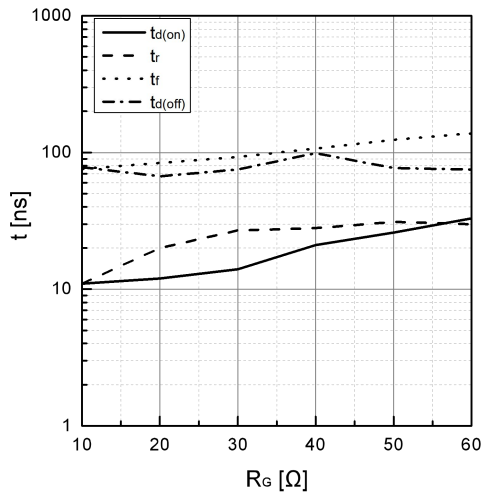


Fig 9. Typical switching times as a function of R_G

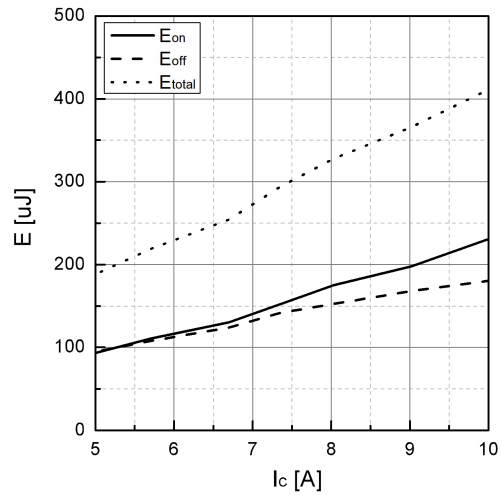


Fig 10. Typical switching energy losses as a function of I_c

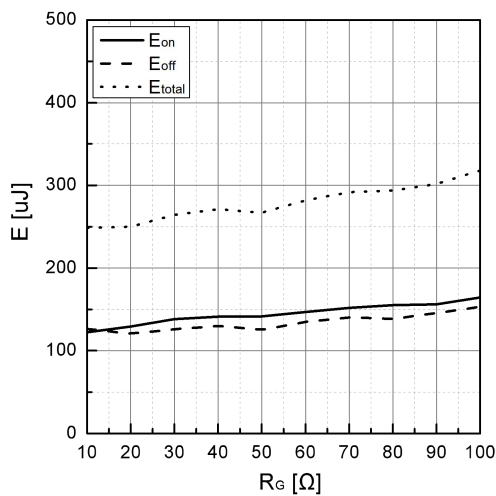


Fig 11. Typical switching energy losses as a function of R_G

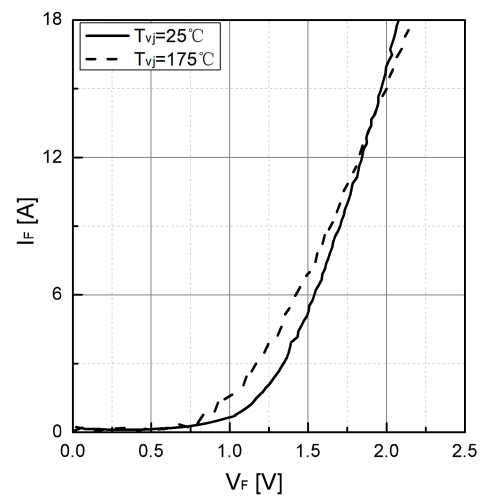


Fig 12. Typical I_F as a function of V_F

Typical performance characteristics

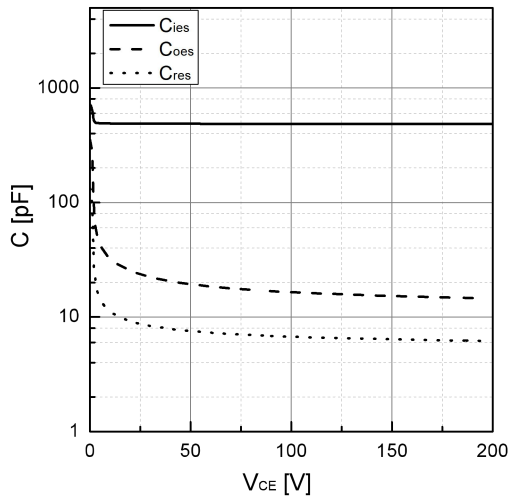


Fig 13. Typical capacitance as a function of V_{CE}
($f=1\text{MHz}$, $V_{GE}=0\text{V}$)

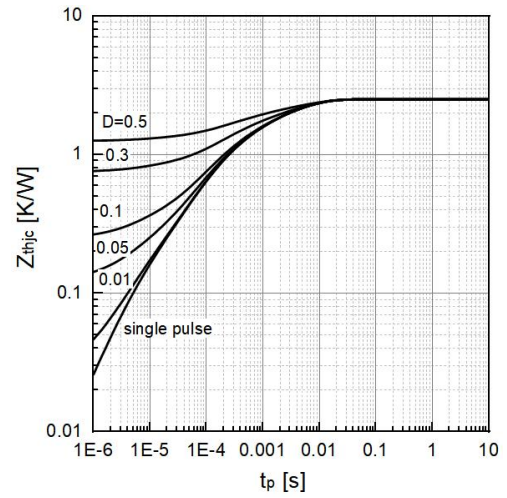
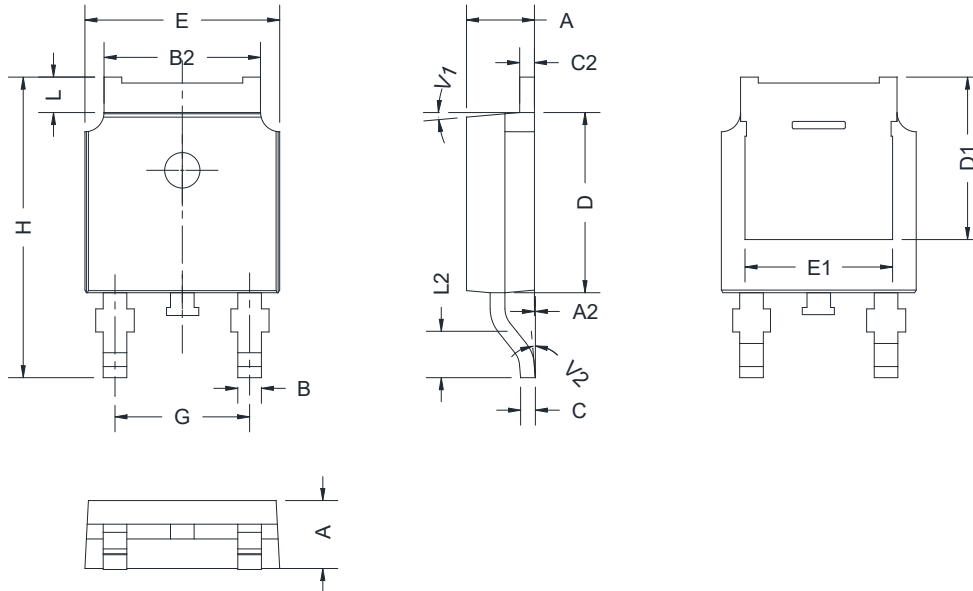


Fig 14. Transient thermal impedance of IGBT

Package dimension

TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10	-	2.50	0.083	-	0.098
A2	0	-	0.10	0	-	0.004
B	0.66	-	0.86	0.026	-	0.034
B2	5.18	-	5.48	0.202	-	0.216
C	0.40	-	0.60	0.016	-	0.024
C2	0.44	-	0.58	0.017	-	0.023
D	5.90	-	6.30	0.232	-	0.248
D1	5.30 REF			0.209 REF		
E	6.40	-	6.80	0.252	-	0.268
E1	4.63	-	-	0.182	-	-
G	4.47	-	4.67	0.176	-	0.184
H	9.50	-	10.70	0.374	-	0.421
L	1.09	-	1.21	0.043	-	0.048
L2	1.35	-	1.65	0.053	-	0.065
V1	-	7°	-	-	7°	-
V2	0°	-	6°	0°	-	6°

Revision history

Date	Revision	Changes
2024-04-17	Rev 1.1	Update
2025-01-13	Rev 1.2	Update
2025-04-08	Rev 1.3	Character Update
2025-12-23	Rev 1.4	Add marking specification
2026-06-23	Rev 1.5	Update Thermal

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